

20A, 350V N-Channel, Logic Level, Voltage Clamping IGBTs

November 2003

Features

- · Logic Level Gate Drive
- Internal Voltage Clamp
- ESD Gate Protection
- T₁ = 175°C
- Ignition Energy Capable

Description

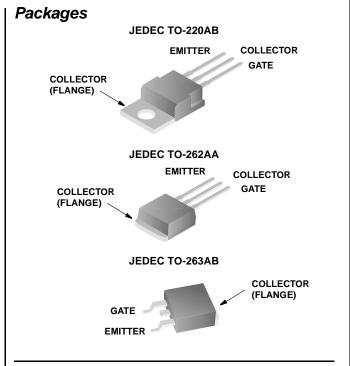
This N-Channel IGBT is a MOS gated, logic level device which is intended to be used as an ignition coil driver in automotive ignition circuits. Unique features include an active voltage clamp between the collector and the gate which provides Self Clamped Inductive Switching (SCIS) capability in ignition circuits. Internal diodes provide ESD protection for the logic level gate. Both a series resistor and a shunt resistor are provided in the gate circuit.

PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
HGTP20N35G3VL	T0-220AB	20N35GVL
HGT1S20N35G3VL	T0-262AA	20N35GVL
HGT1S20N35G3VLS	T0-263AB	20N35GVL

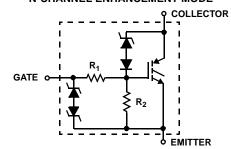
NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in the tape and reel, i.e., HGT1S20N35G3VLS9A.

The development type number for this device is TA49076.



Terminal Diagram

N-CHANNEL ENHANCEMENT MODE



HGTP20N35G3VL

Absolute Maximum Ratings T_C = +25°C, Unless Otherwise Specified

	HGT1S20N35G3VL HGT1S20N35G3VLS	UNITS
Collector-Emitter Bkdn Voltage At 10mA, $R_{GF} = 1k\Omega$	375	V
Emitter-Collector Bkdn Voltage At 10mA BV _{ECS}	24	V
Collector Current Continuous At $V_{GE} = 5.0V$, $T_C = +25^{\circ}C$, Figure 7 I_{C25}	20	Α
At $V_{GE} = 5.0V$, $T_{C} = +100^{\circ}C$	20	Α
Gate-Emitter-Voltage (Note)V _{GES}	±10	V
Inductive Switching Current At L = 2.3mH, T _C = +25° C	21	Α
At L = 2.3 mH, $T_C = +150$ °C	16	Α
Collector to Emitter Avalanche Energy At L = 2.3mH, T _C = +25°C E _{AS}	500	mJ
Power Dissipation Total At T _C = +25°CP _D	150	W
Power Dissipation Derating T _C > +25°C	1.0	W/°C
Operating and Storage Junction Temperature Range	-40 to +175	°C
Maximum Lead Temperature for SolderingT _L	260	°C
Electrostatic Voltage at 100pF, 1500 Ω	6	KV
NOTE: May be exceeded if I _{GEM} is limited to 10mA.		

Specifications HGTP20N35G3VL, HGT1S20N35G3VL, HGT1S20N35G3VLS

Electrical Specifications $T_C = +25^{\circ}C$, Unless Otherwise Specified

		TEST CONDITIONS		LIMITS			
PARAMETERS	SYMBOL			MIN	TYP	MAX	UNITS
Collector-Emitter Breakdown Voltage	BV _{CES}	$I_C = 10$ mA, $V_{GE} = 0$ V	T _C = +175°C	310	345	380	V
			$T_{\rm C} = +25^{\rm o}{\rm C}$	320	350	380	V
			$T_{\rm C} = -40^{\rm o}{\rm C}$	320	355	390	V
Collector-Emitter Breakdown Voltage	BV _{CER}	$I_{C} = 10\text{mA}$ $V_{GE} = 0\text{V}$ $R_{GE} = 1\text{k}\Omega$	T _C = +175°C	300	340	375	V
			$T_{\rm C} = +25^{\rm o}{\rm C}$	315	345	375	V
			$T_{\rm C} = -40^{\rm o}{\rm C}$	315	350	390	V
Gate-Emitter Plateau Voltage	V _{GEP}	I _C = 10A V _{CE} = 12V	T _C = +25°C	-	3.7	-	V
Gate Charge	Q _{G(ON)}	I _C = 10A V _{GE} = 5V V _{CE} = 12V	T _C = +25°C	-	28.7	-	nC
Collector-Emitter Clamp Bkdn. Voltage	BV _{CE(CL)}	$I_C = 10A$ $R_G = 0\Omega$	T _C = +175°C	325	360	395	V
Emitter-Collector Breakdown Voltage	BV _{ECS}	I _C = 10mA	$T_{\rm C} = +25^{\rm o}{\rm C}$	20	32	-	V
Collector-Emitter Leakage Current	I _{CES}	V _{CE} = 250V	$T_{\rm C} = +25^{\rm o}{\rm C}$	-	-	5	μΑ
		V _{CE} = 250V	T _C = +175°C	-	-	250	μΑ
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C = 10A V _{GE} = 4.5V	$T_{\rm C} = +25^{\rm o}{\rm C}$	-	1.3	1.6	V
			T _C = +175°C	-	1.25	1.5	V
		I _C = 20A V _{GE} = 5.0V	$T_{\rm C} = +25^{\rm o}{\rm C}$	-	1.6	2.8	V
			T _C = +175°C	-	1.9	3.5	V
Gate-Emitter Threshold Voltage	V _{GE(TH)}	$I_C = 1 \text{mA}$ $V_{CE} = V_{GE}$	T _C = +25°C	1.3	1.8	2.3	V
Gate Series Resistance	R ₁		T _C = +25°C	-	1.0	-	kΩ
Gate-Emitter Resistance	R ₂		$T_{\rm C} = +25^{\rm o}{\rm C}$	10	17	25	kΩ
Gate-Emitter Leakage Current	I _{GES}	V _{GE} = ±10V		±400	±590	±1000	μΑ
Gate-Emitter Breakdown Voltage	BV _{GES}	I _{GES} = ±2mA		±12	±14	-	V
Current Turn-Off Time-Inductive Load	t _{D(OFF)I} + t _{F(OFF)I}	$\begin{split} &I_{C} = 10\text{A}, \ R_{G} = 25\Omega, \\ &L = 550\mu\text{H}, \ R_{L} = 26.4\Omega, \ V_{GE} = 5\text{V}, \\ &V_{CL} = 300\text{V}, \ T_{C} = +175^{\circ}\text{C} \end{split}$		-	15	30	μs
Inductive Use Test	I _{scis}	$L = 2.3 \text{mH},$ $V_G = 5 \text{V},$ $R_G = 0 \Omega$	$T_{\rm C} = +150^{\rm o}{\rm C}$	16	-	-	Α
			$T_{\rm C} = +25^{\rm o}{\rm C}$	21	-	-	А
Thermal Resistance	$R_{ heta JC}$		•	-	-	1.0	°C/W

Typical Performance Curves

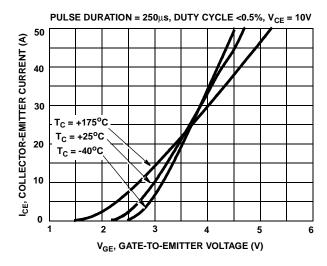


FIGURE 1. TRANSFER CHARACTERISTICS

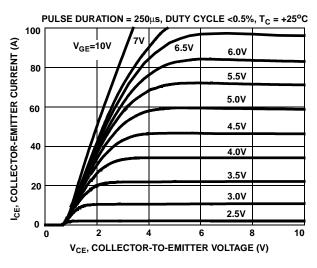
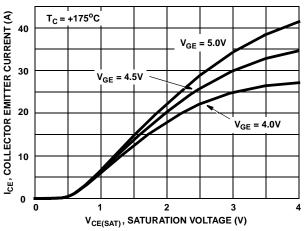


FIGURE 2. SATURATION CHARACTERISTICS



0 2 $V_{CE(SAT)}$, SATURATION VOLTAGE (V)

FIGURE 3. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

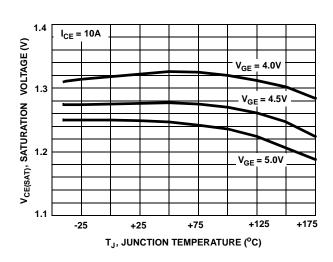


FIGURE 5. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

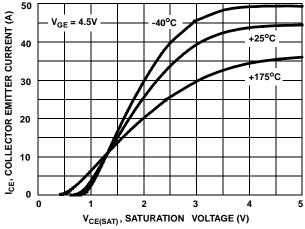


FIGURE 4. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF SATURATION VOLTAGE

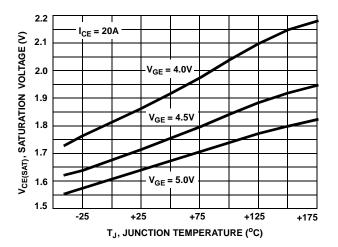
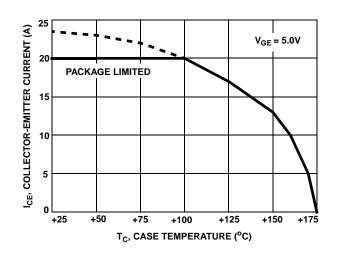


FIGURE 6. SATURATION VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE

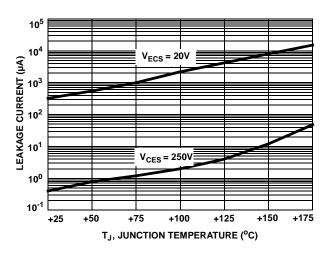
Typical Performance Curves (Continued)



1.2 | I_{CE} = 1mA | I_{CE} = 1m

FIGURE 7. COLLECTOR-EMITTER CURRENT AS A FUNCTION OF CASE TEMPERATURE

FIGURE 8. NORMALIZED THRESHOLD VOLTAGE AS A FUNCTION OF JUNCTION TEMPERATURE



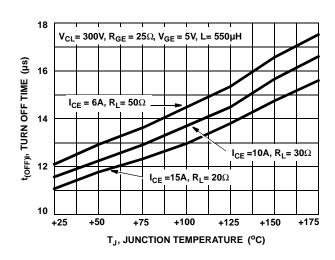
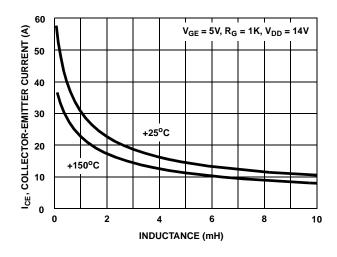


FIGURE 9. LEAKAGE CURRENT AS A FUNCTION OF JUNCTION TEMPERATURE

FIGURE 10. TURN-OFF TIME AS A FUNCTION OF JUNCTION TEMPERATURE



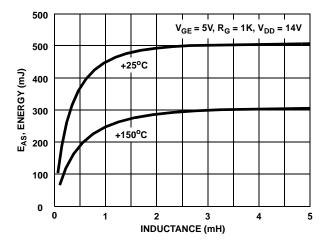


FIGURE 11. SELF CLAMPED INDUCTIVE SWITCHING CURRENT vs INDUCTANCE

FIGURE 12. SELF CLAMPED INDUCTIVE SWITCHING ENERGY vs INDUCTANCE

Typical Performance Curves (Continued)

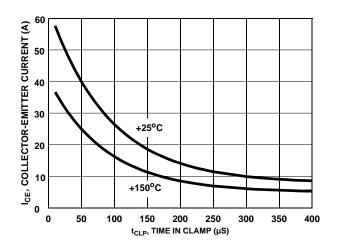


FIGURE 13. SELF CLAMPED INDUCTIVE SWITCHING CURRENT VS TIME IN CLAMP

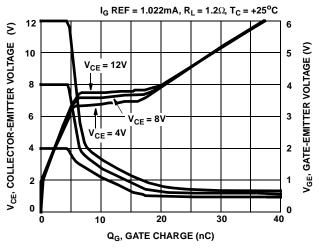


FIGURE 15. GATE CHARGE

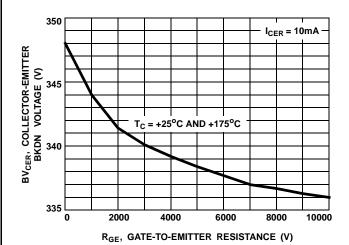


FIGURE 17. BREAKDOWN VOLTAGE AS A FUNCTION OF GATE - EMITTER RESISTANCE

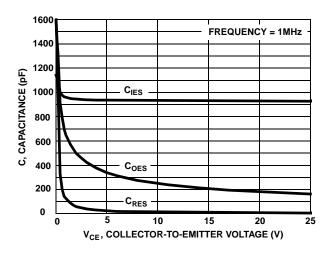


FIGURE 14. CAPACITANCE AS A FUNCTION OF COLLECTOR-EMITTER VOLTAGE

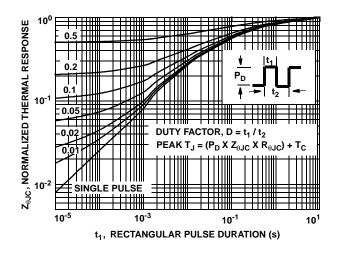


FIGURE 16. NORMALIZED TRANSIENT THERMAL IMPEDANCE, JUNCTION TO CASE

Test Circuits

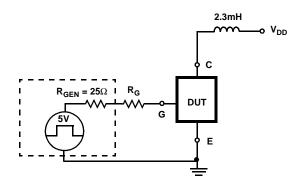


FIGURE 18. USE TEST CIRCUIT

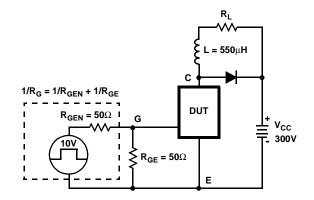


FIGURE 19. INDUCTIVE SWITCHING TEST CIRCUIT

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